

T2322B

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed primarily for ac power switching. The gate sensitivity of these triacs permits the use of economical transistorized or integrated circuit control circuits, and it enhances their use in low-power phase control and load-switching applications.

- Very High Gate Sensitivity
- Low On-State Voltage at High Current Levels
- Glass-Passivated Chip for Stability
- Small, Rugged Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Device Marking: Device Type, e.g., T2322B, Date Code

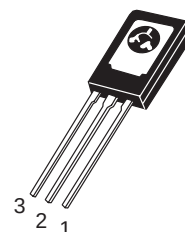
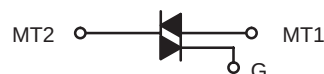
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ ($T_J = 25$ to 110°C , Gate Open)	V_{DRM} , V_{RRM}	200	Volts
On-State RMS Current ($T_C = 70^\circ\text{C}$) (Full Cycle Sine Wave 50 to 60 Hz)	$I_{\text{T(RMS)}}$	2.5	Amps
Peak Non-Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, $T_C = 70^\circ\text{C}$)	I_{TSM}	25	Amps
Circuit Fusing Consideration ($t = 8.3$ ms)	I^2t	2.6	A^2s
Peak Gate Power (Pulse Width ≤ 10 μs , $T_C = 70^\circ\text{C}$)	P_{GM}	10	Watts
Average Gate Power ($t = 8.3$ ms, $T_C = 70^\circ\text{C}$)	$P_{\text{G(AV)}}$	0.5	Watt
Peak Gate Current (Pulse Width = 10 μs , $T_C = 70^\circ\text{C}$)	I_{GM}	0.5	Amp
Operating Junction Temperature Range	T_J	-40 to $+110$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$
Mounting Torque (6-32 Screw) ⁽²⁾	—	8.0	in. lb.



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TRIACS 2.5 AMPERES RMS 200 VOLTS



TO-225AA
(formerly TO-126)
CASE 077
STYLE 5

PIN ASSIGNMENT

	PIN ASSIGNMENT
1	Main Terminal 1
2	Main Terminal 2
3	Gate

ORDERING INFORMATION

Device	Package	Shipping
T2322B	TO225AA	500/Box

T2322B

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}, \text{ Gate Open}$)	I_{DRM}, I_{RRM}	— —	— 0.2	10 0.75	μA mA
$T_J = 25^{\circ}\text{C}$ $T_J = 110^{\circ}\text{C}$					

ON CHARACTERISTICS

Peak On-State Voltage ⁽¹⁾ ($I_{TM} = \pm 10 \text{ A}$)	V_{TM}	—	1.7	2.2	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$) All Quadrants	I_{GT}	—	—	10	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega, T_C = 25^{\circ}\text{C}$)	V_{GT}	—	1.0	2.2	Volts
Gate Non-Trigger Voltage ($V_D = 12 \text{ V}, R_L = 100 \Omega, T_C = 110^{\circ}\text{C}$)	V_{GD}	0.15	—	—	Volts
Holding Current ($V_D = 12 \text{ V}, I_T \text{ (Initiating Current)} = \pm 200 \text{ mA}, \text{ Gate Open}$)	I_H	—	15	30	mA
Gate Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}, I_{TM} = 10 \text{ A pk}, I_G = 60 \text{ mA}, t_r = 0.1 \mu\text{sec}$)	t_{gt}	—	1.8	2.5	μs

DYNAMIC CHARACTERISTICS

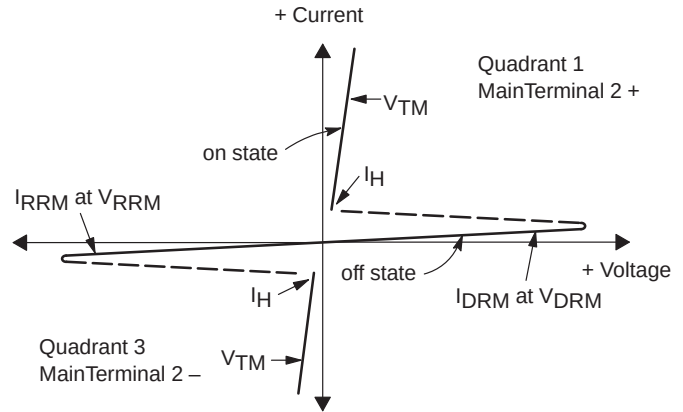
Critical Rate-of-Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}, \text{ Exponential Waveform}, T_C = 100^{\circ}\text{C}$)	dv/dt	10	100	—	$\text{V}/\mu\text{s}$
Critical Rate-of-Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}, I_{TM} = 3.5 \text{ A pk}, \text{ Commutating } di/dt = 1.26 \text{ A/ms}, \text{ Gate Unenergized}, T_C = 90^{\circ}\text{C}$)	$dv/dt(c)$	1.0	4.0	—	$\text{V}/\mu\text{s}$

(1) Pulse Test: Pulse Width $\leq 1.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

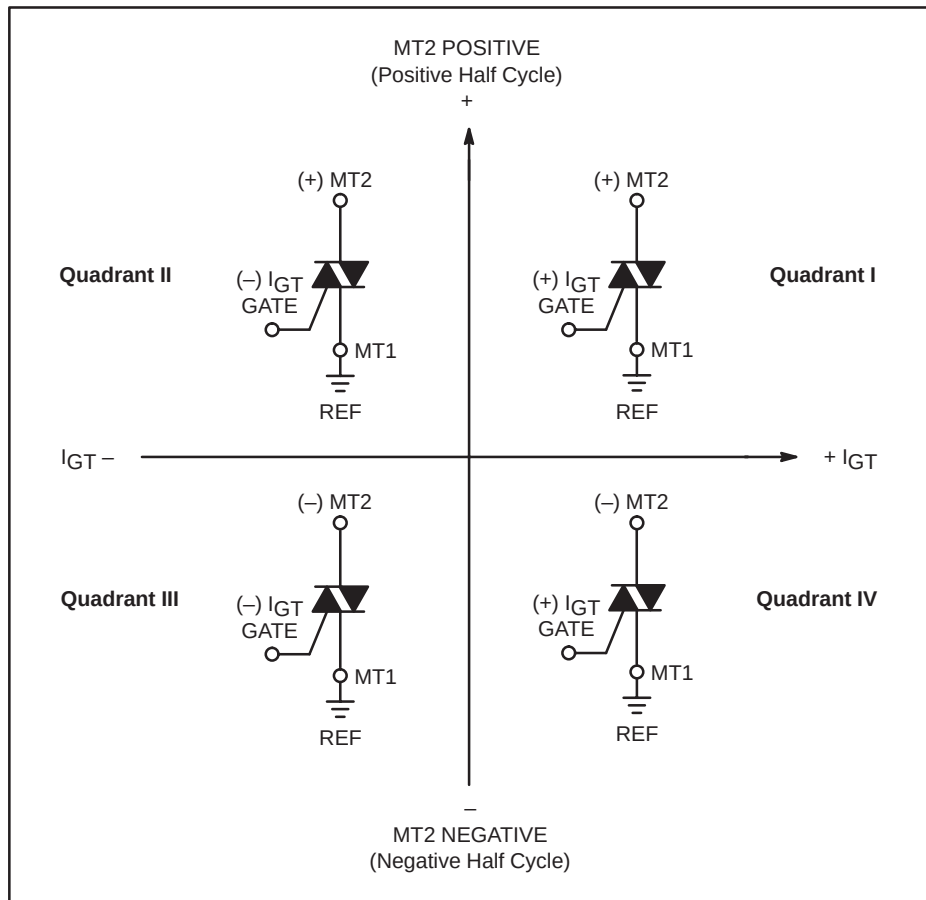
T2322B

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac

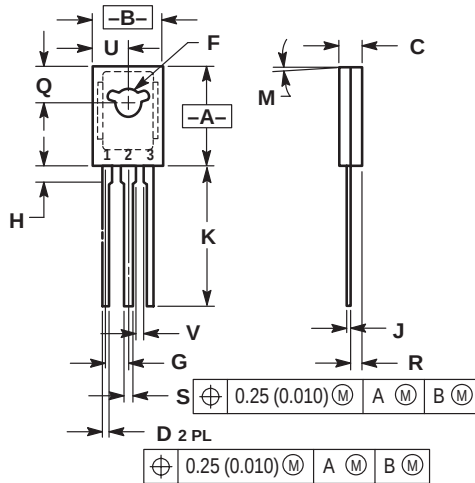


All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used.

T2322B

PACKAGE DIMENSIONS

TO-225AA
(formerly TO-126)
CASE 077-09
ISSUE W



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	—	1.02	—

- STYLE 5:
PIN 1. MT 1
2. MT 2
3. GATE

资料提供 可控硅在线
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